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SEMICONDUCTOR®

November 2013

FQPF9N50C N-Channel QFET[®] MOSFET

500 V, 9 A, 800 mΩ

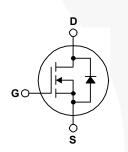
Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction, electronic lamp ballasts based on half bridge topology.

Features

- 9 A, 500 V, $R_{DS(on)}$ = 800 m Ω (Max.) @ V_{GS} = 10 V, I_D = 4.5 A
- Low Gate Charge (Typ. 28 nC)
- Low Crss (Typ. 24 pF)
- 100% Avalanche Tested





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

Symbol	Parameter	FQPF9N50C	Units		
V _{DSS}	Drain-Source Voltage		500	V	
I _D	Drain Current - Continuous (T _C = 25°C	C)	9 *	A	
	- Continuous (T _C = 100	°C)	5.4 *	A	
I _{DM}	Drain Current - Pulsed	(Note 1)	36 *	A	
V _{GSS}	Gate-Source Voltage		± 30	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2) 360		mJ	
I _{AR}	Avalanche Current	(Note 1) 9		A	
E _{AR}	Repetitive Avalanche Energy	(Note 1) 13.5		mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns	
P _D	Power Dissipation ($T_C = 25^{\circ}C$)		44	W	
	- Derate above 25°C		0.35	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Ran	ge	-55 to +150	°C	
ΤL	Maximum lead temperature for soldering 1/8" from case for 5 seconds	purposes,	300	°C	

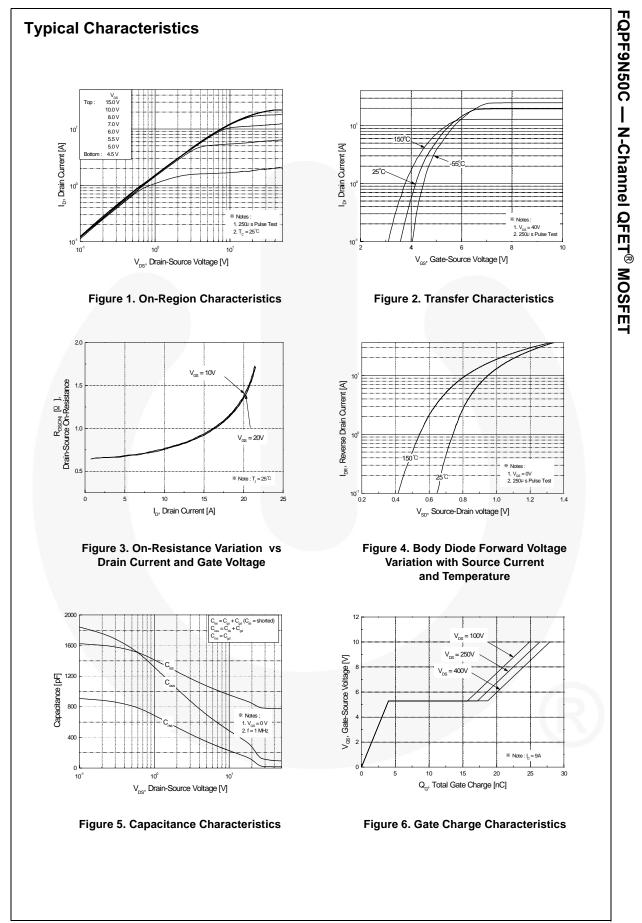
* Drain current limited by maximum junction temperature.

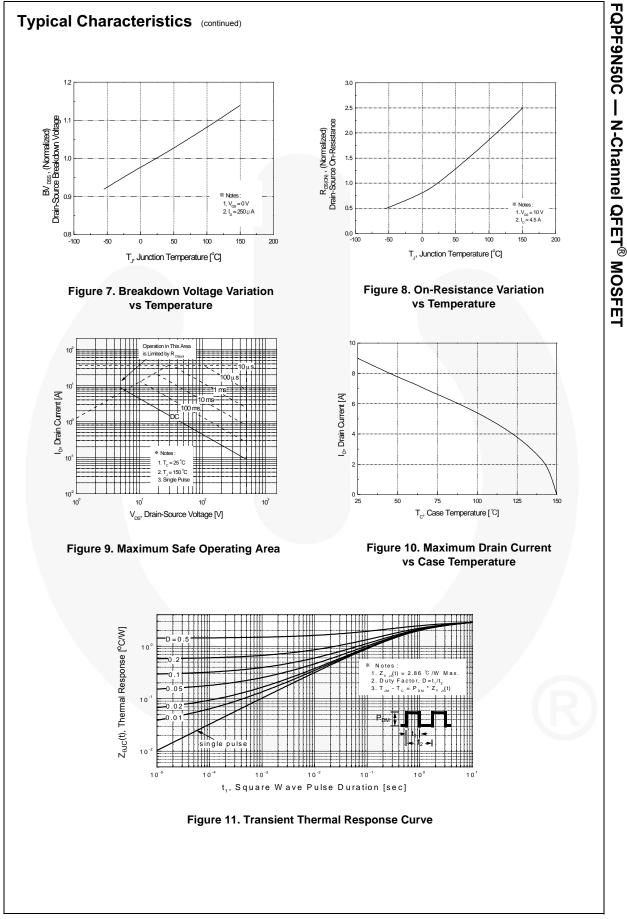
Thermal Characteristics

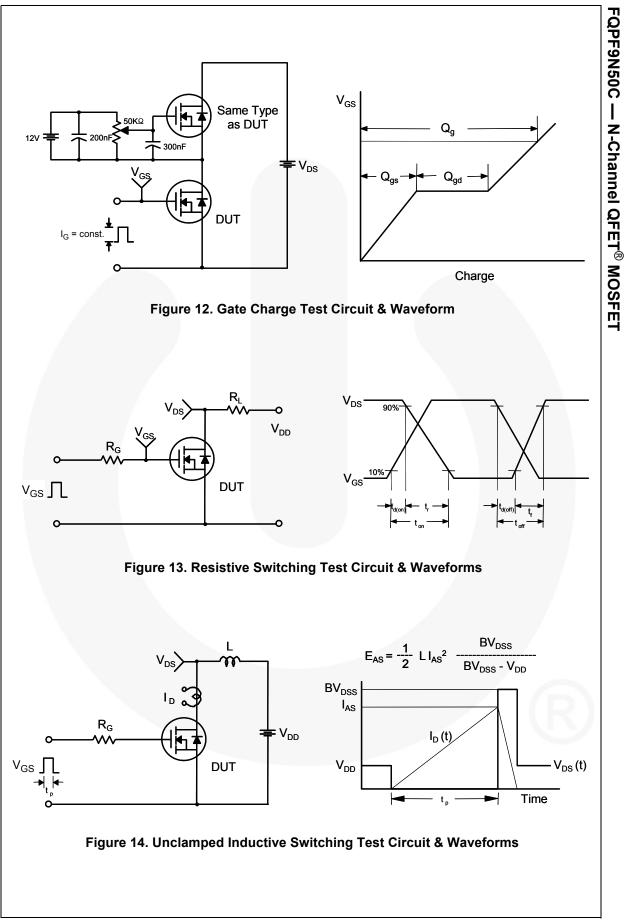
Symbol	Parameter	FQPF9N50C	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.86	°C/W	
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

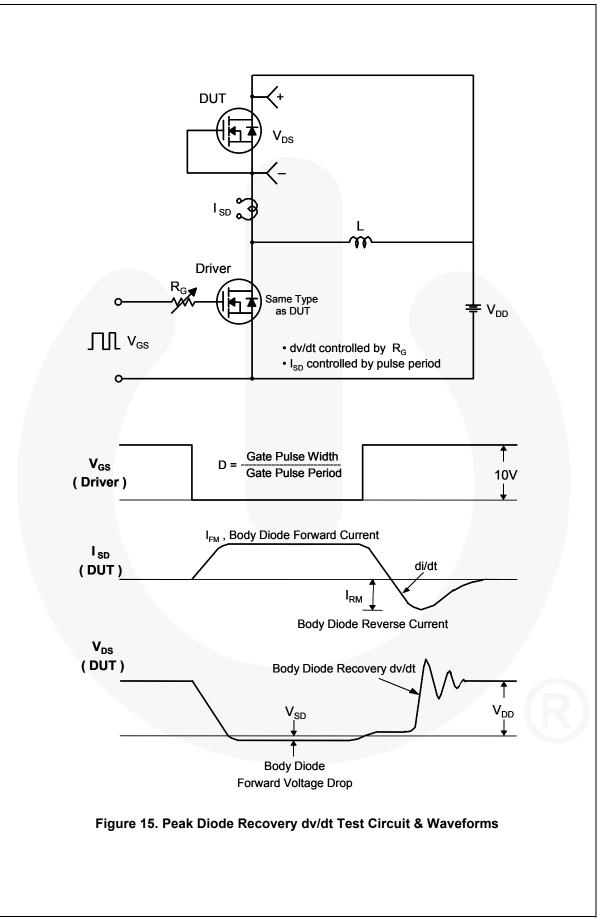
F9N50	er	Top Mark	Pack	age .	Packing Method	Reel	0120	Tape Width		Quantity
FQPF9N50C		FQPF9N50C		20F			A	N/A		50 units
trica	l Chara	cteristics	T _c = 25°C unl	ess otherv	vise noted.					
ol		Parameter			Test Conditions		Min	Тур	Max	Unit
Chara	cteristic	S								·
S Drain-Source Breakdown Voltage			$V_{GS} = 0 V, I_{D} = 250 \mu A$			500			V	
	Breakdown Voltage Temperature Coefficient		$I_D = 250 \ \mu\text{A}$, Referenced to 25°C				0.57		V/°C	
Ze	Zero Gate Voltage Drain Current			$V_{DS} = 500 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 400 \text{ V}, T_C = 125^{\circ}\text{C}$					1 10	μA μA
G	Gate-Body Leakage Current, Forward			$V_{GS} = 30 \text{ V}, V_{DS} = 0 \text{ V}$					100	nA
	Gate-Body Leakage Current, Reverse			$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$					-100	nA
	cteristics			- 63					100	101
			_	Vpc =	V _{GS} , I _D = 250 μA	-	2.0		4.0	V
n) St	Gate Threshold Voltage Static Drain-Source On-Resistance			$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 4.5 \text{ A}$				0.65	0.8	Ω
		nsconductance	_	Vns =	40 V, I _D = 4.5 A	-		6.5		S
			_	00	. 0					
amic (Characte	eristics								
In	nput Capaci	tance		V _{DS} =	25 V, V _{GS} = 0 V,			790	1030	pF
0	output Capa	citance		f = 1.0				130	170	pF
R	everse Trar	nsfer Capacitanc	e					24	30	pF
ahina	Charac	ariatiaa								
	y Charac t urn-On Dela		_					18	45	
			_	V _{DD} =	250 V, I _D = 9 A,			-	-	ns
	urn-On Rise			R _G = 2	25 Ω			65	140 195	ns
	urn-Off Dela urn-Off Fall	-				(Note 4)		93 64	195	ns
	otal Gate Cl	-			100.1/1 0.4			28	35	ns
		ů.			400 V, I _D = 9 A,			4		-
	ate-Source			V _{GS} =	10 V	(Note 4)				nC
G	Sate-Drain C	narge				(11018 4)		15		nC
n-Sou		le Character	istics ar	nd Mar	kimum Ratings					
		ontinuous Drain-			•				9	Α
		Ilsed Drain-Sour							36	A
		Diode Forward			$0 \text{ V}, \text{ I}_{\text{S}} = 9 \text{ A}$				1.4	V
			Vollago							ns
		,		1	-					μC
		, ,	unction temper	•				2.00		μο
tive rating nH, I _{AS} = 9 A, di/dt ≤	g : pulse-width I 9 A, V _{DD} = 50 V 200 A/µs, V _{DD}	covery Time covery Charge imited by maximum ju $C_{\rm R_G} = 25 \Omega$, starting $\leq BV_{\rm DSS}$, starting T _J = rating temperature.	J TJ = 25°C.	dl _F / d	0 V, I _S = 9 A, t = 100 A/μs			335 2.95		

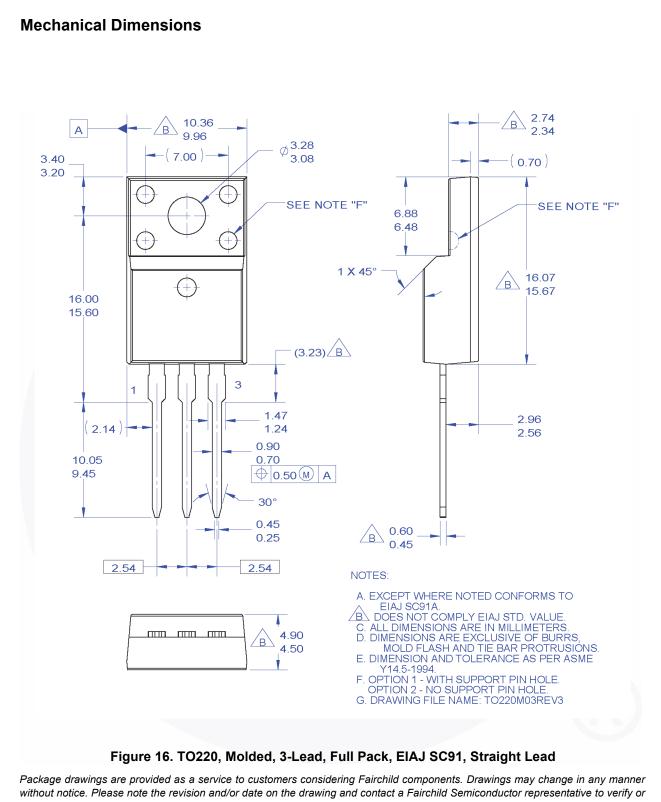
FQPF9N50C — N-Channel QFET[®] MOSFET











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FQPF9N50C —

N-Channel QFET[®] MOSFET



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Obsolete

Not In Production

Datasheet contains specifications on a product that is discontinued by Fairchild

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Rev. 166

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